

What is claimed is:

1. A LVTSCR-like structure having one or more diodes formed in a p-well of the structure.
2. A method of increasing the holding voltage of a LVTSCR structure, comprising forming at least one p-n junction inside a p-well of the structure.
3. A method of increasing the holding voltage of a LVTSCR-like structure, comprising providing an alternative current path through a p-well of the structure, other than purely the p-material of the p-well.
4. A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.
5. A method of claim 4, wherein the lower resistance current path takes the form of at least one p-n junction formed in the p-well.
6. A method of claim 4, wherein at least one diode is formed in the p-well which provides a low resistance current path once the voltage across the at least one diode is exceeded.
7. A method of increasing the holding voltage of a LVTSCR-like structure, comprising providing an alternative current path through a p-well of the structure.
8. A method of claim 7, wherein the alternative current path becomes the main current path when the current through the LVTSCR exceeds the saturation current through the resistor formed by the p-well and the p+ regions of the diodes.

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